General Description

The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS® Generic series is optimized for extreme switching performance to minimize

Absolute Maximum Ratings at T_j=25°C unless otherwise noted

PARAMETER	SYMBOL	VALUE	UNIT
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	47	A
Continuous drain current[1], T_C=100 °C		29.7	
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	141	A
Continuous diode forward current[1], T_C=25 °C	I_S	47	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	141	A
Power dissipation[3], T_C=25 °C	P_D	241	W
Single pulsed avalanche energy[5]	E_{AS}	975	mJ
MOSFET dv/dt ruggedness, V_{DS} 480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} 480 V, I_{SD} D	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Thermal resistance, junction-case	R	0.52	°C/W
Thermal resistance, junction-ambient[4]	R	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Drain-source breakdown voltage	BV_{DSS}	600			V	V_{GS}=0 V, I_D=1 mA
		650				V_{GS}=0 V, I_D=1 mA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	3.5		4.5	V	V_{DS}=V_{GS}, I_D=1 mA
Drain-source on-state resistance	$R_{DS(ON)}$		54	60	m	V_{GS}=10 V, I_D=16 A
			140			V_{GS}=10 V, I_D=16 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			1	A	V_{DS}=600 V, V_{GS}=0 V
Gate resistance	R_G		8.6			= 1 MHz, Open drain

Dynamic Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Input capacitance	C_{iss}		2372		pF	V_{GS}=0 V, V_{DS}=50 V, Hz
Output capacitance	C_{oss}		200		pF	
Reverse transfer capacitance	C_{rss}		4.1		pF	
Effective output capacitance, energy related	$C_{o(er)}$		122		pF	V_{GS} = 0 V, V_{DS} = 0V-400V
Effective output capacitance, time related	$C_{o(tr)}$		707		pF	
Turn-on delay time	$t_{d(on)}$		32.4		ns	V_{GS}=10 V, V_{DS}=400 V, R_G=2 I_D=20 A
Rise time	t_r		42.8		ns	
Turn-off delay time	$t_{d(off)}$		101.2		ns	
Fall time	t_f		37.2		ns	

Gate Charge Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Total gate charge	Q_g		56.2		nC	V_{GS}=10 V, V_{DS}=400 V, I_D=20 A
Gate-source charge	Q_{gs}		13.1		nC	
Gate-drain charge	Q_{gd}		20.6		nC	
Gate plateau voltage	$V_{plateau}$		5.78		V	

Body Diode Characteristics

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Diode forward voltage	V_{SD}			1.3	V	I_S=47 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		382		ns	V_R=400 V, I_S=20 A,
Reverse recovery charge	Q_{rr}		5.8		C	
Peak reverse recovery current	I_{rrm}		28.5		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of R is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100 V, V_{GS}=10 V, L=75 mH, starting T_j=25 °C.

Electrical Characteristics Diagrams

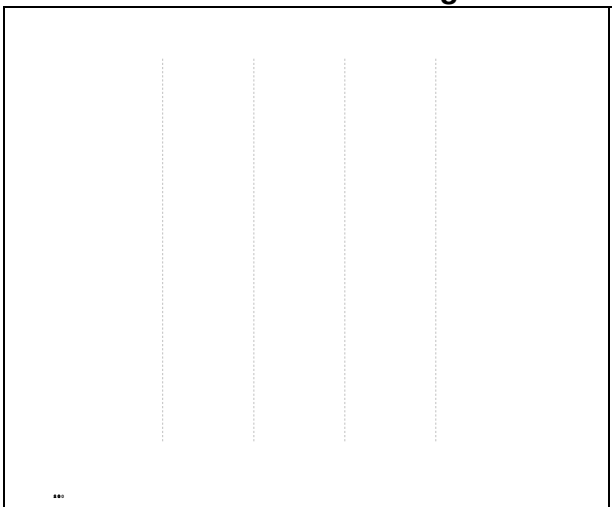

Figure 1. Typ. output characteristics

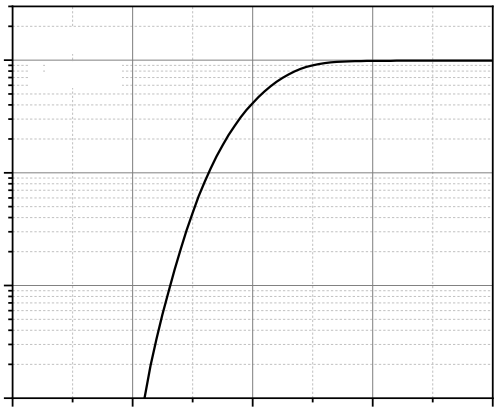

Figure 2. Typ. transfer characteristics

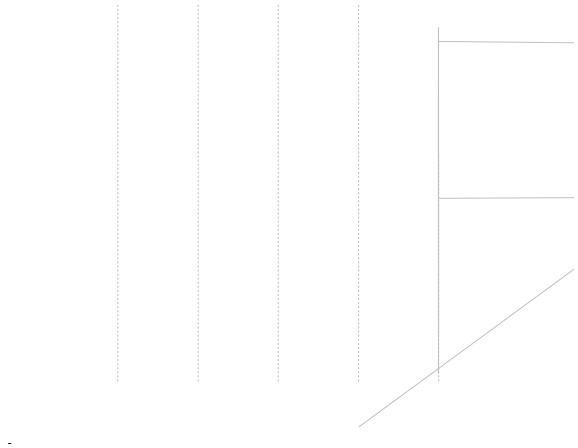

Figure 3. Typ. capacitances

Figure 4. Typ. gate charge

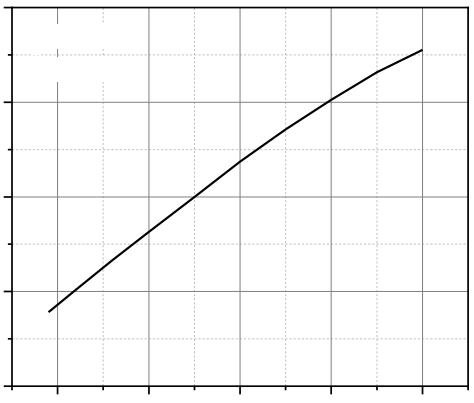

Figure 5. Drain-source breakdown voltage

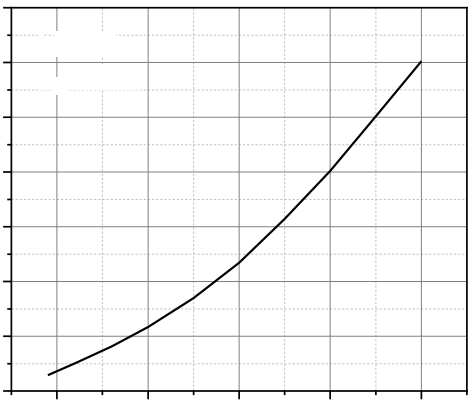

Figure 6. Drain-source on-state resistance

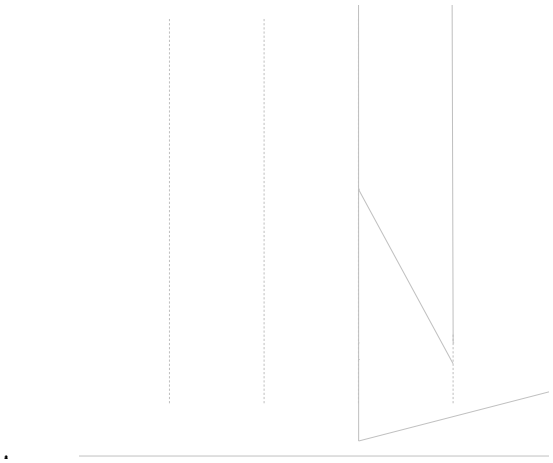

Figure 7. Threshold voltage

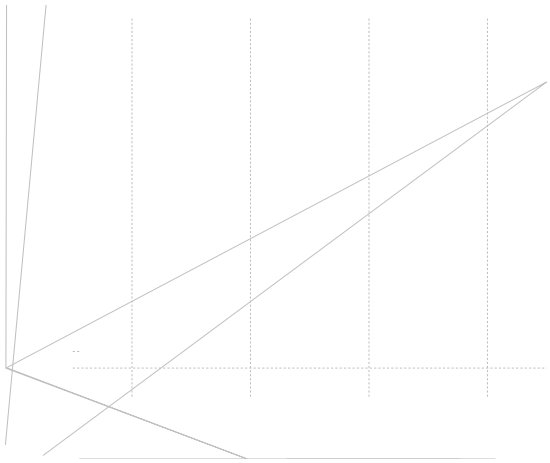

Figure 8. Forward characteristic of body diode

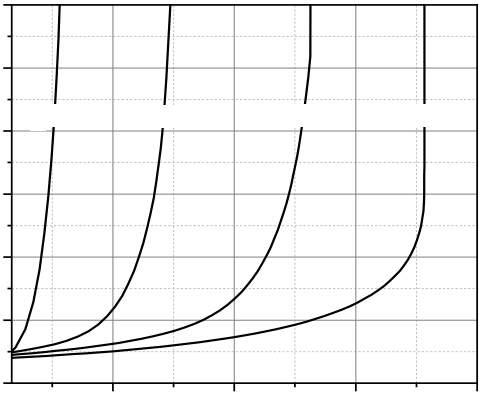

Figure 9. Drain-source on-state resistance

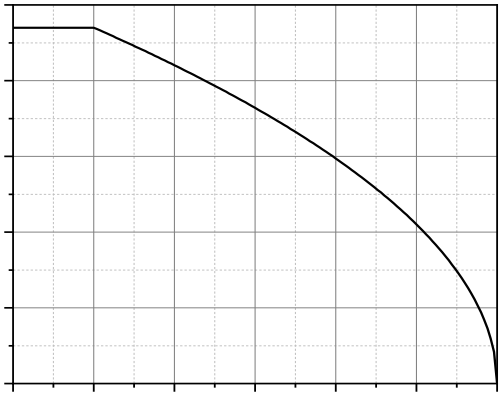

Figure 10. Drain current

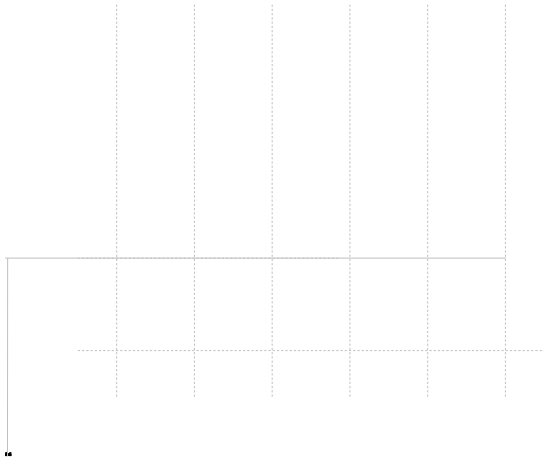

Figure 11. Typ. Coss stored energy

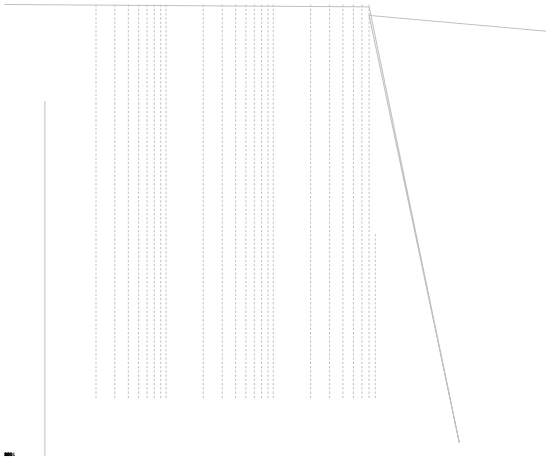

Figure 12. Safe operation area for TC=25

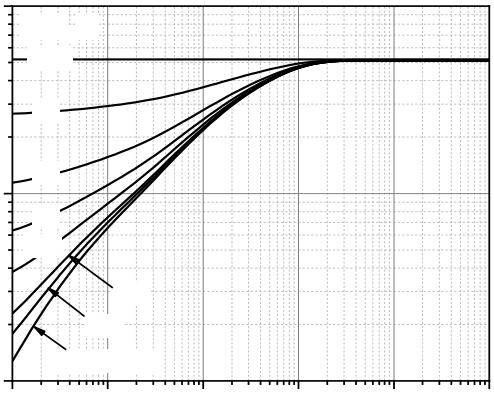

Figure 13. Max transient thermal impedance

Test circuits and waveforms

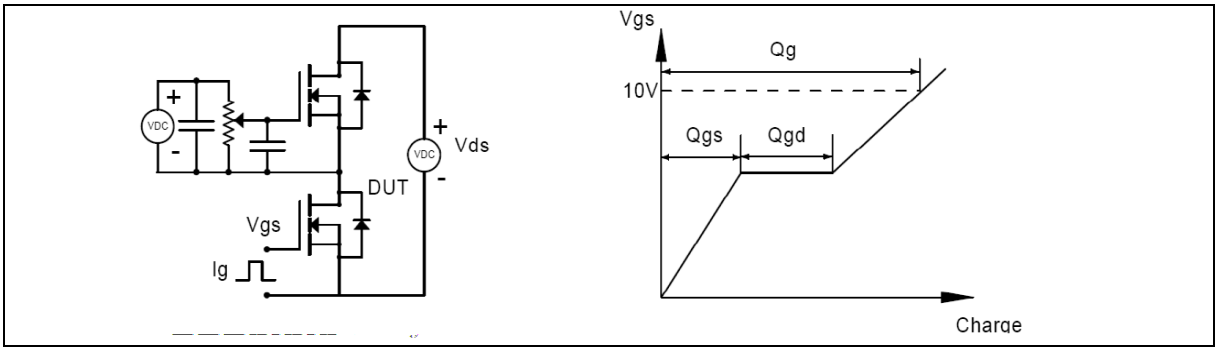

Figure 1. Gate charge test circuit & waveform

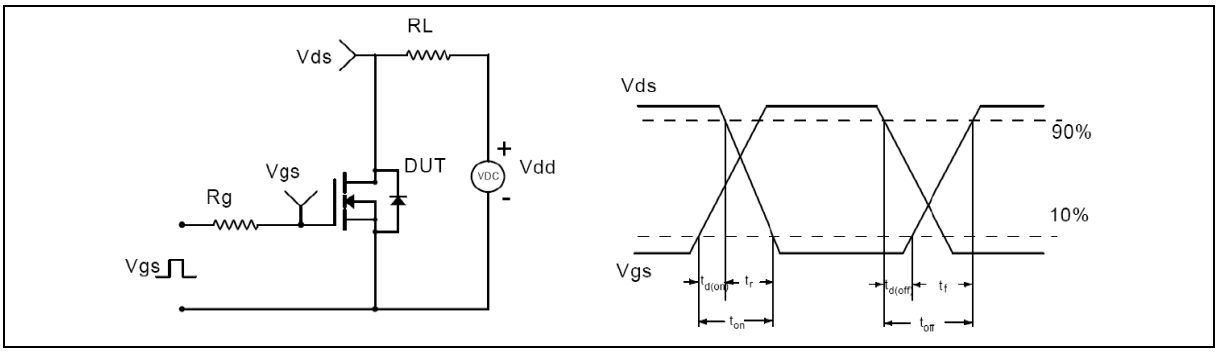

Figure 2. Switching time test circuit & waveforms

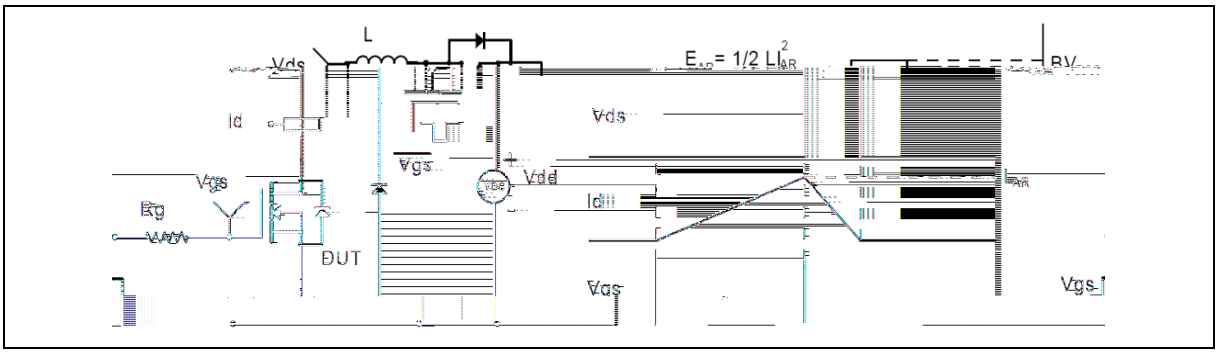

Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

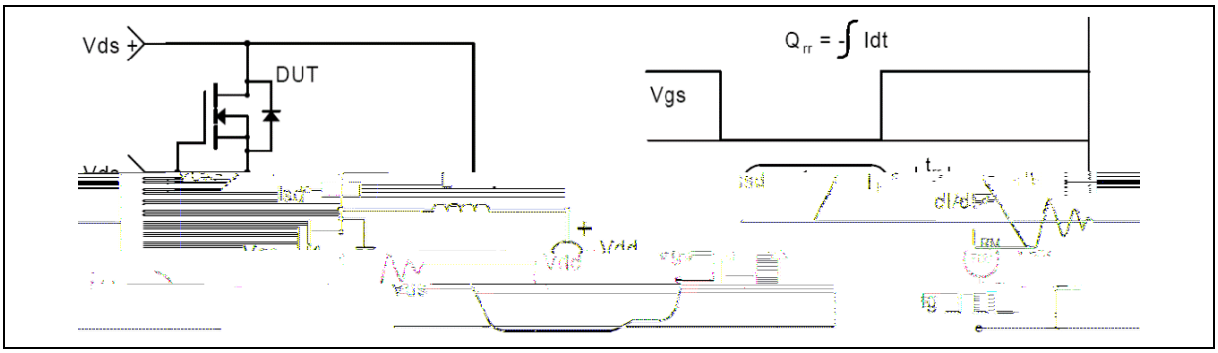

Figure 4. Diode reverse recovery test circuit & waveforms

Package Information

Symbol	mm		
	Min	Nom	Max
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0.00	-	0.15
a'	0.00	-	0.15
b	1.16	-	1.26
b1	1.15	1.2	1.22
b2	1.96	-	2.06
b3	1.95	2.00	2.02
b4	2.96	-	3.06
b5	2.96	3.00	3.02
b6	-	-	2.25
b7	-	-	3.25
c	0.59	-	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70		